TOSHIBA RF POWER AMPLIFIER MODULE

# S-AV23AL, S-AV23AH, S-AV23AVH

VHF POWER AMPLIFIER MODULE

S-AV23AL :  $f = 135 \sim 150 MHz$ S-AV23AH :  $f = 150 \sim 163 MHz$ S-AV23AVH :  $f = 160 \sim 175 MHz$ 

#### MAXIMUM RATINGS (Tc = 25°C)

| CHARACTERISTIC                   | SYMBOL               | RATING  | UNIT |
|----------------------------------|----------------------|---------|------|
| DC Supply Voltage                | $v_{CC}$             | 11      | V    |
| DC Supply Voltage                | $ m V_{BB}$          | 6       | V    |
| Input Power                      | Pi                   | 400     | mW   |
| Operating Case Temperature Range | T <sub>c (opr)</sub> | -30~100 | °C   |
| Storage Temperature Range        | $\mathrm{T_{stg}}$   | -40~110 | °C   |

26.6±0.2 -R1.5±0.2 21.3±1  $23.9 \pm 1$ 6. 5MAX **INPUT**  $v_{BB}$ 2.  $v_{cc}$  $\frac{3}{4}$ . OUTPUT GROUND (FLANGE) JEDEC **EIAJ** 

5-22K

**TOSHIBA** 

Weight: 3.5g

Unit in mm

# ELECTRICAL CHARACTERISTICS (Tc = 25°C)

| CHARACTERISTIC   | SYMBOL              | TEST CONDITION  | MIN.  | TYP. | MAX. | UNIT |
|------------------|---------------------|---|---|------|------|------|
| Frequency Range  | f <sub>range</sub>  | _   | 135   | _    | 175  | MHz  |
| Output Power     | Po                  |   | 2.7   | _    | l —  | W    |
| Power Gain       | $G_{p}$             | Pi=200mW  |   | _    | _    | dB   |
| Total Efficiency | $\eta_{\mathbf{T}}$ | $V_{\rm CC}$ =7.5V, $V_{\rm BB}$ =5V                              | 35  | _    | _    | %    |
| Input VSWR       | VSWRin              | $Z_G = Z_L = 50\Omega$  | _   | 1.5  | 2.5  | _    |
| Harmonics        | HRM                 |   | _   | _    | -20  | dB   |
| Load Mismatch    | _                   | $V_{CC}=9V$ $V_{BB}=5V$ $Pi=200mW$ $VSWR load 20:1 all phase$     | No Degradation  |      | _    |      |
| Stability        | _                   | $V_{CC}=6\sim9V$ $V_{BB}=5V$ $Pi=200mW$ $VSWR load 6:1 all phase$ | All spurious<br>output than 60dB<br>below desired<br>signal |      | _    |      |

#### CAUTION

This product has intersetting cap. Please pay attention for exceeding stress and foreign matter in your application. And not to take away the cap.

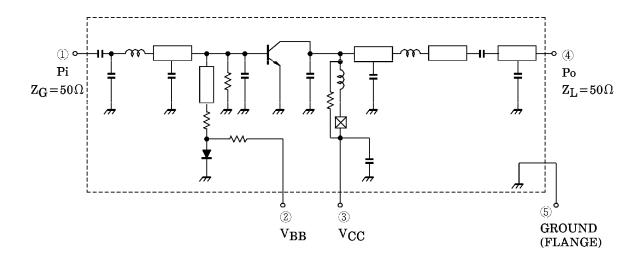
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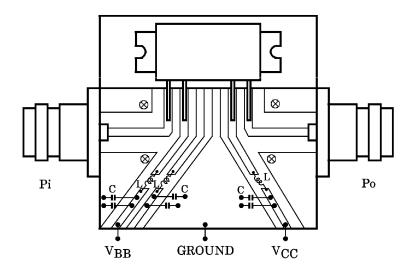
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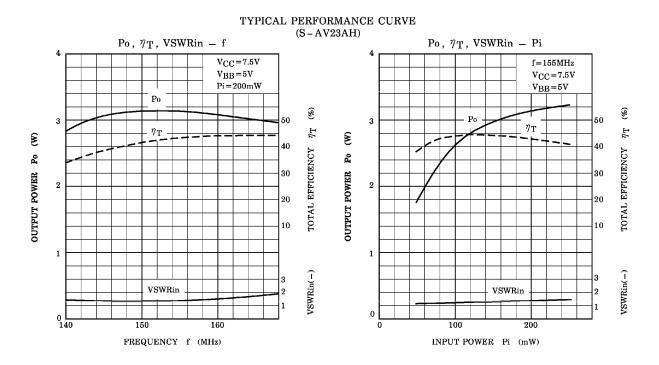
# **SCHEMATIC**

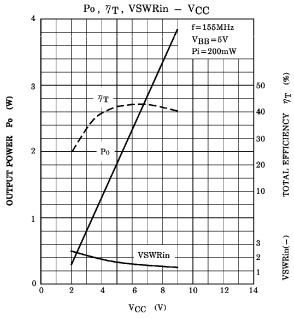


### TEST FIXTURE



C : 22000pF,  $10\mu F$  PARALLEL L :  $\phi 0.5$  ENAMEL WIRE 3ID, 5T





# CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.